

## SOT-89 Plastic-Encapsulate Transistors

### Features

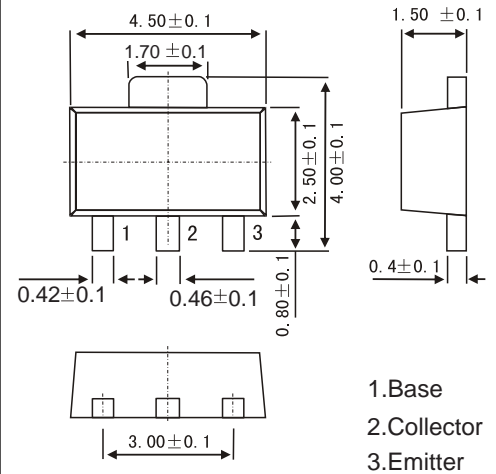
- Collector Current Capability  $I_C=-0.2A$
- Collector Emitter Voltage  $V_{CEO}=-40V$
- Compliment to PXT3904
- PNP Transistors

### MECHANICAL DATA

- Case style:SOT-89molded plastic
- Mounting position:any

### SOT-89

Unit:mm



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	-40	V
Collector - Emitter Voltage	$V_{CEO}$	-40	
Emitter - Base Voltage	$V_{EBO}$	-6	
Collector Current - Continuous	$I_C$	-0.2	A
Collector Power Dissipation	$P_C$	0.5	W
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{stg}$	-55 to 150	

### PACKAGE INFORMATION

Device	Package	Shipping
PXT3906 (KXT3906)	SOT-89	1000/Tape&Reel

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{CBO}$	$I_C = -100 \mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{CEO}$	$I_C = -1 mA, I_B = 0$	-40			
Emitter-base breakdown voltage	$V_{EBO}$	$I_E = -100 \mu A, I_C = 0$	-6			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = -30 V, I_E = 0$			-50	nA
Collector-emitter cut-off current	$I_{CEX}$	$V_{CE} = -30 V, V_{BE(off)} = -3V$			-50	
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -6V, I_C = 0$			-50	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 mA, I_B = -1mA$ $I_C = -50 mA, I_B = -5mA$			-0.25 -0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10 mA, I_B = -1mA$ $I_C = -50 mA, I_B = -5mA$	-0.65		-0.85 -0.95	
DC current gain	$h_{FE}$	$V_{CE} = -1V, I_C = -0.1mA$	60			
		$V_{CE} = -1V, I_C = -1mA$	80			
		$V_{CE} = -1V, I_C = -10mA$	100	300		
		$V_{CE} = -1V, I_C = -50mA$	60			
		$V_{CE} = -1V, I_C = -100mA$	30			
Noise figure	NF	$V_{CE} = -5V, I_C = -0.1mA, f = 10Hz-15.7kHz, R_S = 1K\Omega$			4	dB
Delay time	$t_d$	$I_C = -10mA, I_{B1} = -I_{B2} = -1mA$			35	ns
Rise time	$t_r$				35	
Storage time	$t_s$				225	
Fall time	$t_f$				75	
Collector output capacitance	$C_{ob}$	$V_{CB} = -5V, I_E = 0, f = 1MHz$			4.5	pF
Emitter capacitance	$C_e$	$V_{EB} = -0.5V, I_C = 0, f = 1MHz$			10	
Transition frequency	$f_T$	$V_{CE} = -20V, I_C = -10mA, f = 100MHz$	250			MHz

### Marking

Marking	2A
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